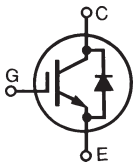
IXYS

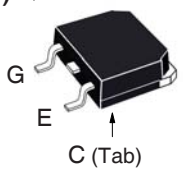
High Voltage, High Gain BIMOSFET™ Monolithic Bipolar MOS Transistor

IXBH20N300
IXBT20N300

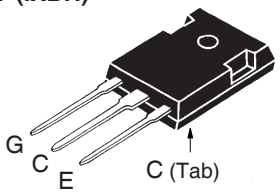
V_{CES} = 3000V
I_{C110} = 20A
$V_{CE(sat)} \leq$ 3.2V



TO-268 (IXBT)



TO-247 (IXBH)



G = Gate C = Collector
E = Emiiter Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_C = 25°C to 150°C	3000	V
V_{CGR}	T_J = 25°C to 150°C, R_{GE} = 1MΩ	3000	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	T_C = 25°C	50	A
I_{C110}	T_C = 110°C	20	A
I_{CM}	T_C = 25°C, 1ms	140	A
SSOA (RBSOA)	V_{GE} = 15V, T_{VJ} = 125°C, R_G = 20Ω	I_{CM} = 130	A
	Clamped Inductive Load	1500	V
P_C	T_C = 25°C	250	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6mm (0.062 in.) from Case for 10s	300	°C
T_{SOLD}	Plastic Body for 10 seconds	260	°C
M_d	Mounting Torque (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0V	3000			V
$V_{GE(th)}$	I_C = 250μA, V_{CE} = V_{GE}	2.5		5.0	V
I_{CES}	V_{CE} = 0.8 • V_{CES}, V_{GE} = 0V			35	μA
	T_J = 125°C			1.5	mA
I_{GES}	V_{CE} = 0V, V_{GE} = ± 20V			±100	nA
$V_{CE(sat)}$	I_C = 20A, V_{GE} = 15V, Note 1		2.7	3.2	V
	T_J = 125°C		3.2		V

Features

- High Blocking Voltage
- Anti-Parallel Diode
- International Standard Packages
- Low Conduction Losses

Advantages

- Low Gate Drive Requirement
- High Power Density

Applications:

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

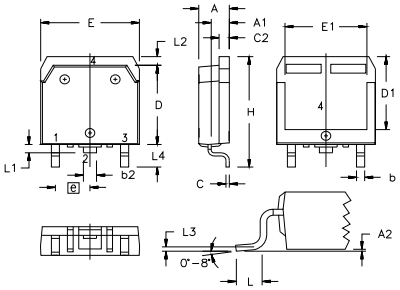
Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	I_C = 20A, V_{CE} = 10V, Note 1	11	18		S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		2230		pF
C_{oes}			92		pF
C_{res}			33		pF
Q_g	I_C = 20A, V_{GE} = 15V, V_{CE} = 1000V		105		nC
Q_{ge}			13		nC
Q_{gc}			45		nC
$t_{d(on)}$	**Resistive Switching Times, T_J = 25°C**		64		ns
t_r	I_C = 20A, V_{GE} = 15V		210		ns
$t_{d(off)}$	V_{CE} = 1250V, R_G = 10Ω		300		ns
t_f			504		ns
$t_{d(on)}$	**Resistive Switching Times, T_J = 125°C**		68		ns
t_r	I_C = 20A, V_{GE} = 15V		540		ns
$t_{d(off)}$	V_{CE} = 1250V, R_G = 10Ω		300		ns
t_f			395		ns
R_{thJC}				0.50	°C/W
R_{thCS}	(TO-247)		0.21		°C/W

Reverse Diode

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
V_F	I_F = 20A, V_{GE} = 0V			2.1	V
t_{rr}	I_F = 10A, V_{GE} = 0V, $-di_F/dt$ = 100A/µs		1.35		µs
I_{RM}	V_R = 100V, V_{GE} = 0V		30		A

Note 1: Pulse test, t ≤ 300µs, duty cycle, d ≤ 2%.

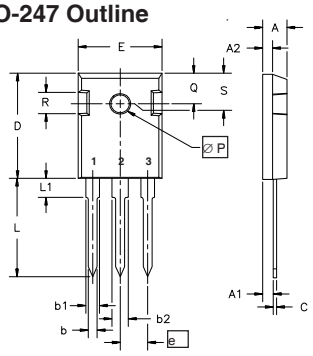
TO-268 Outline



Terminals: 1 - Gate 2,4 - Collector
3 - Emitter

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

TO-247 Outline



Terminals: 1 - Gate 2 - Collector
3 - Emitter

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

Fig. 1. Output Characteristics @ T_J = 25ºC

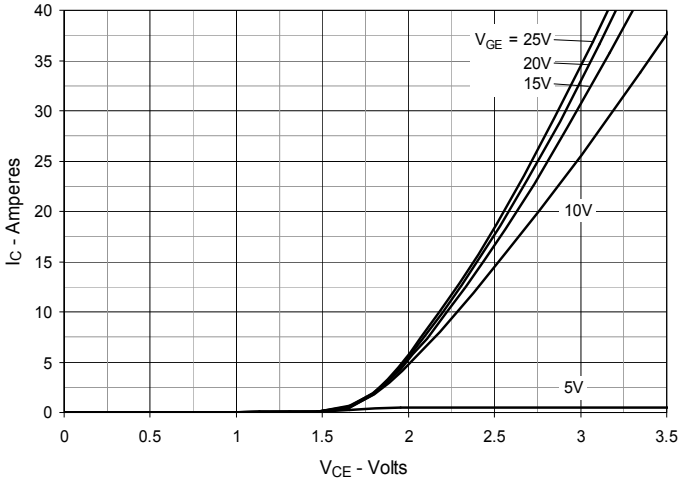


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

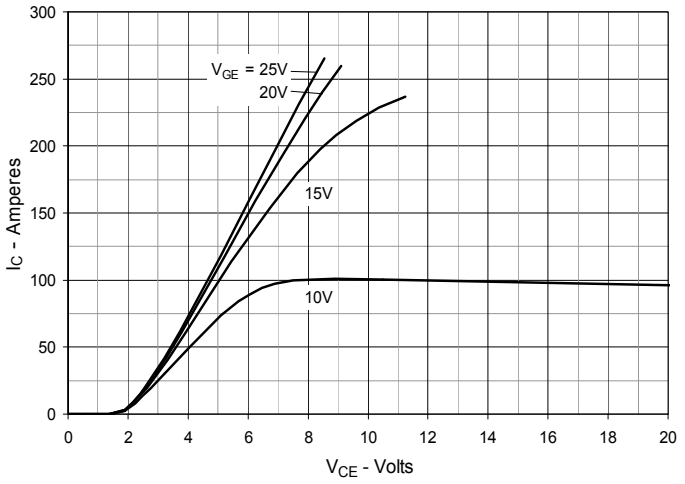


Fig. 3. Output Characteristics @ T_J = 125ºC

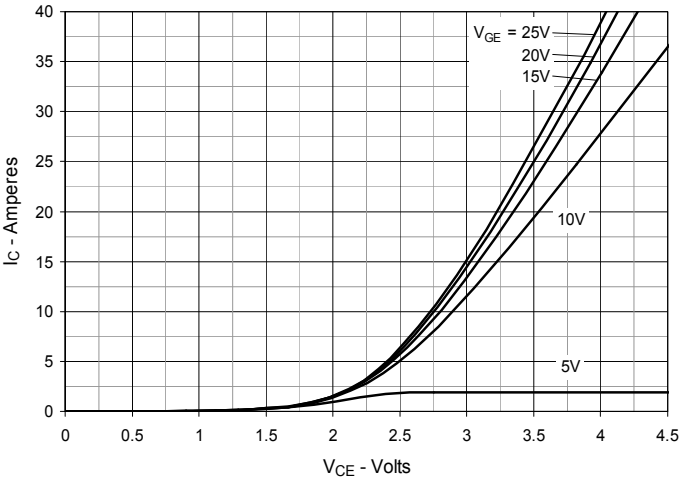


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

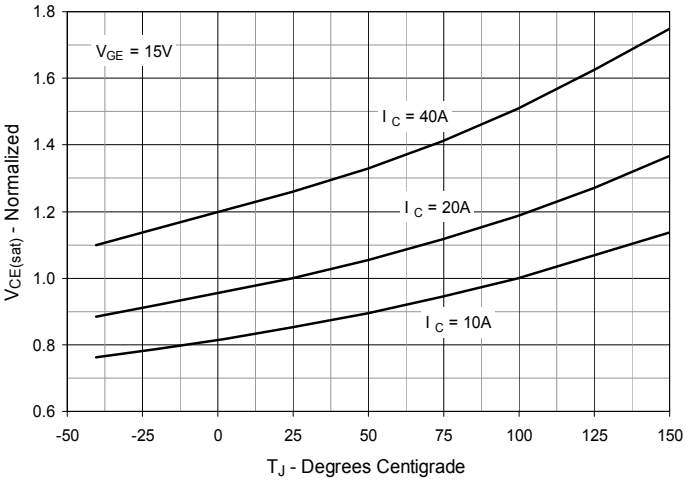


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

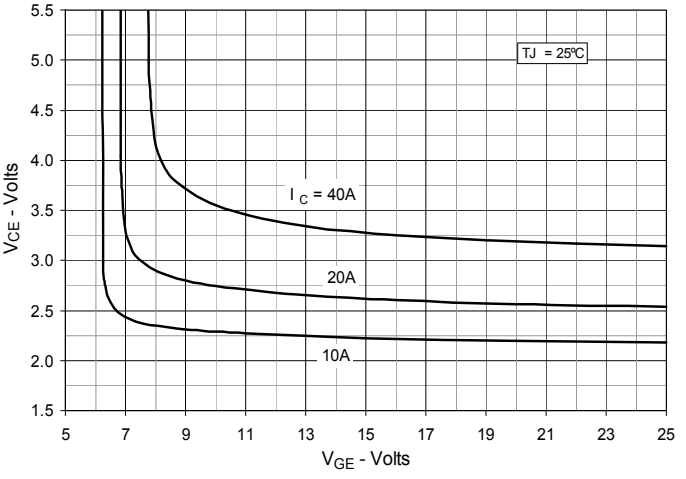


Fig. 6. Input Admittance

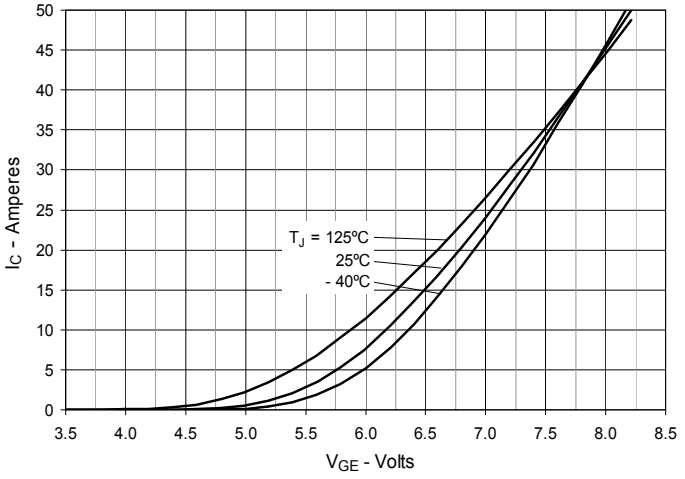


Fig. 7. Transconductance

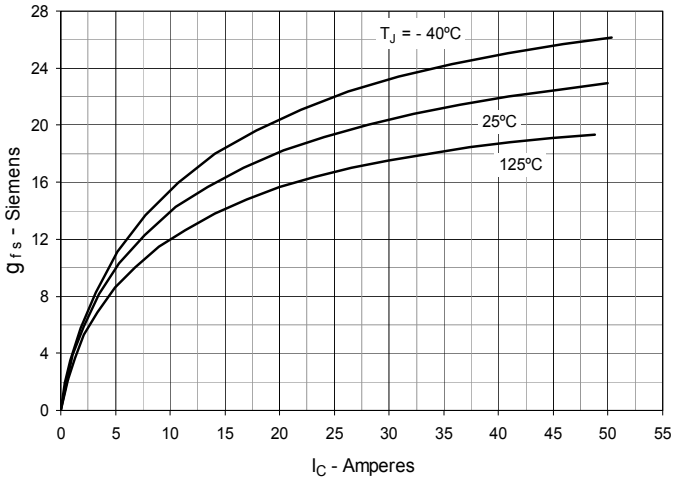


Fig. 8. Forward Voltage Drop of Intrintsic Diode

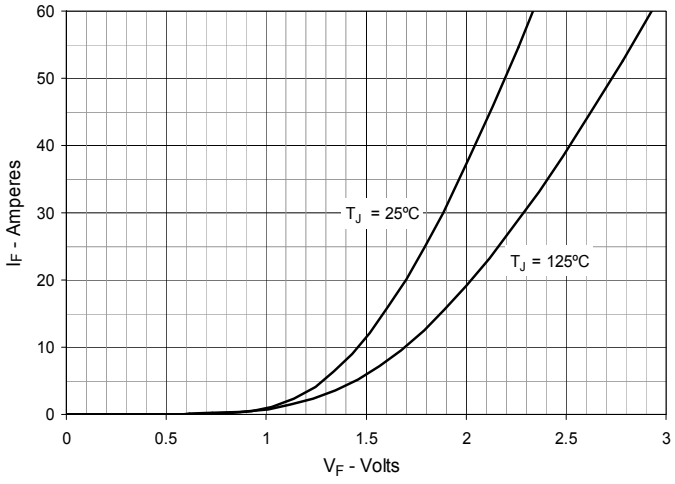


Fig. 9. Gate Charge

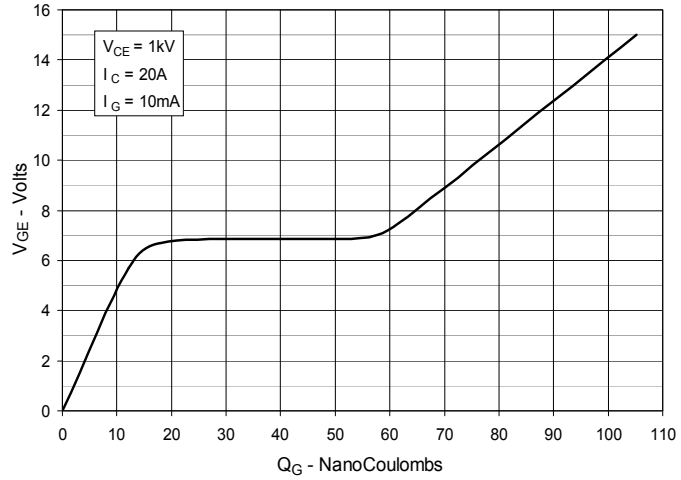


Fig. 10. Capacitance

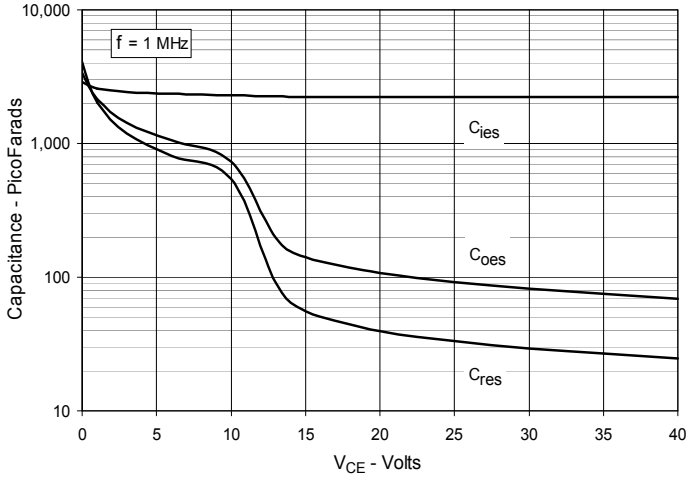


Fig. 11. Reverse-Bias Safe Operating Area

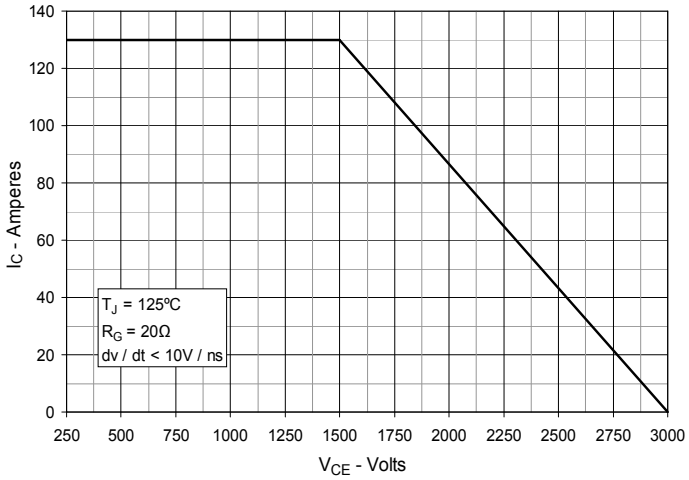


Fig. 12. Maximum Transient Thermal Impedance

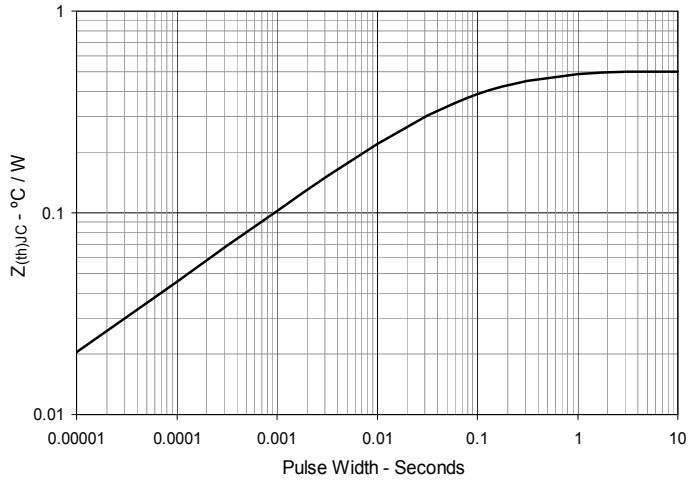


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

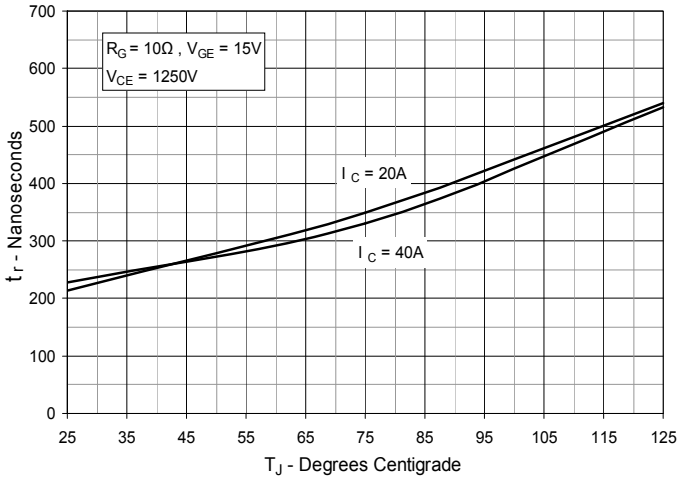


Fig. 14. Resistive Turn-on Rise Time vs. Collector Current

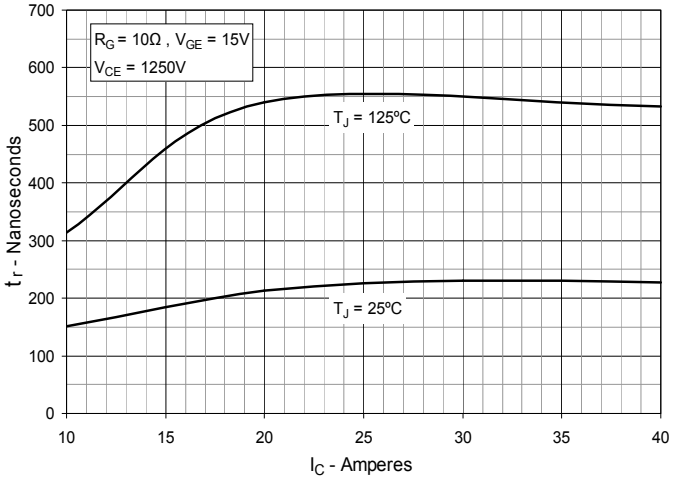


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

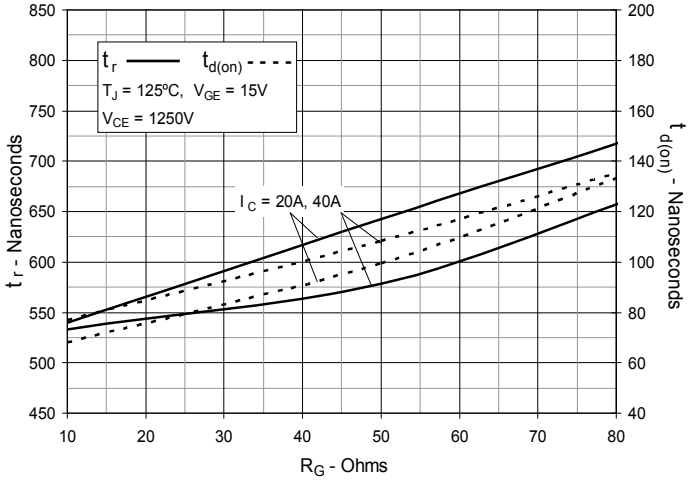


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

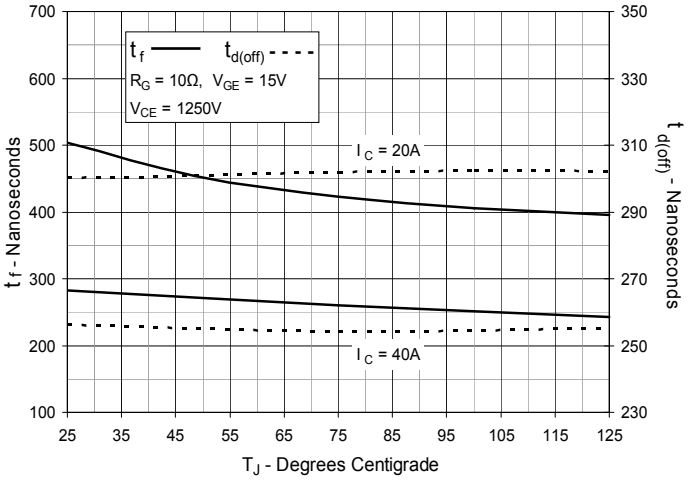


Fig. 17. Resistive Turn-off Switching Times vs. Collector Current

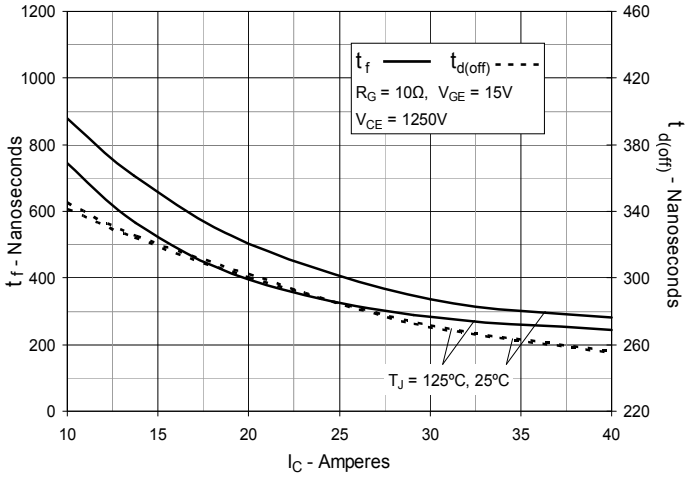


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance